

产品规格书

Specification of products

产品名称:螺旋型晶闸管

产品型号: KP350A

浙江世菱半导体有限公司
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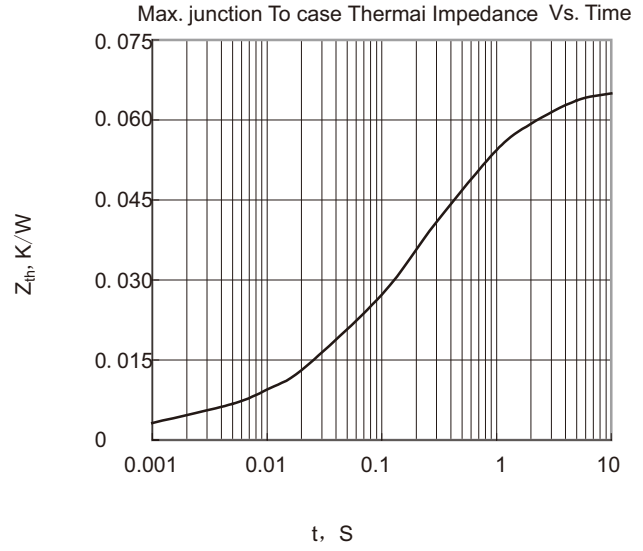
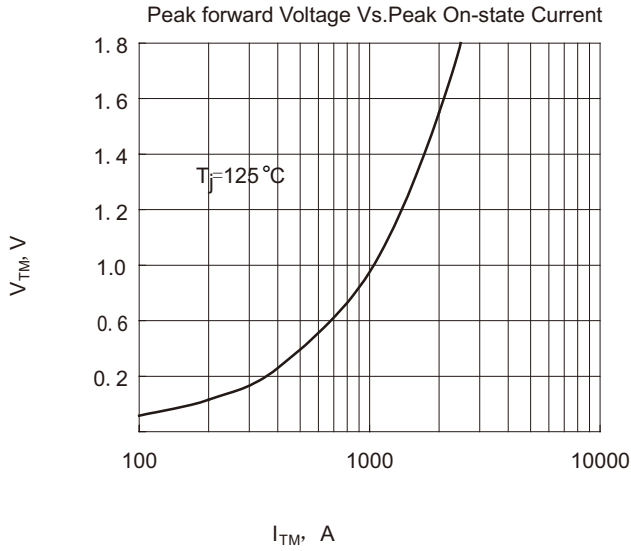
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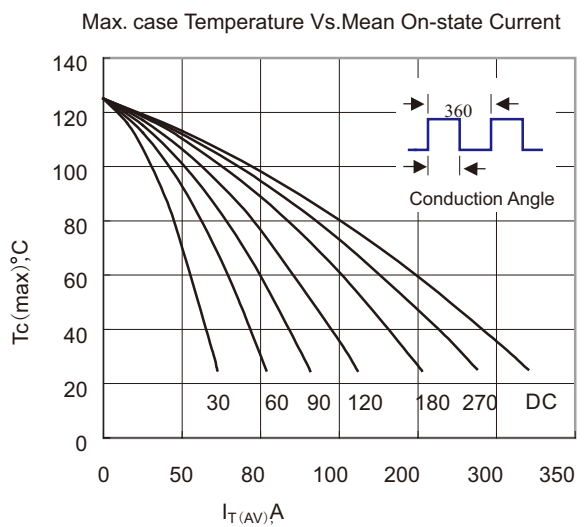
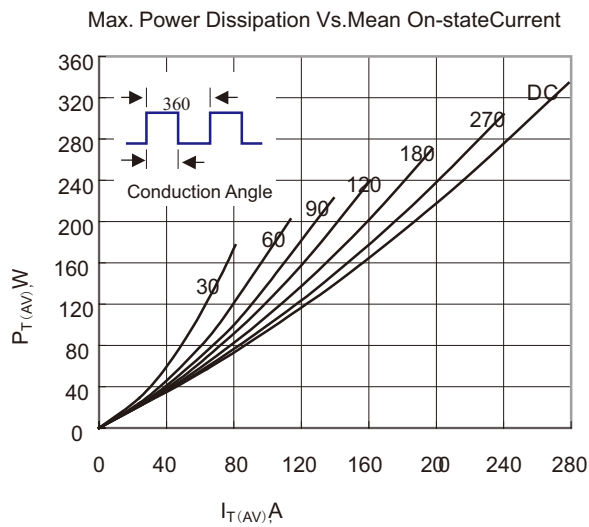
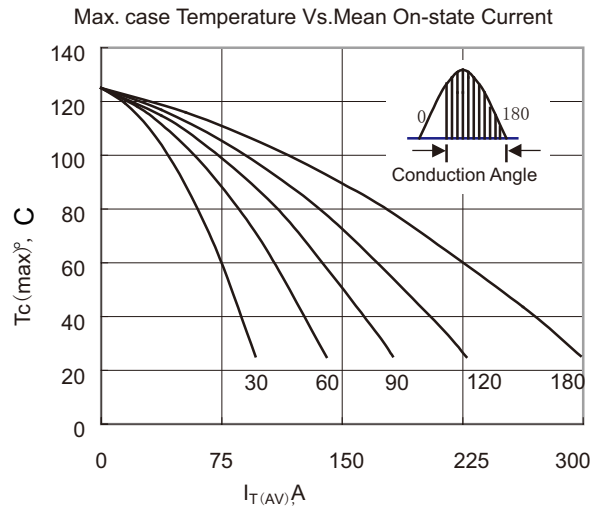
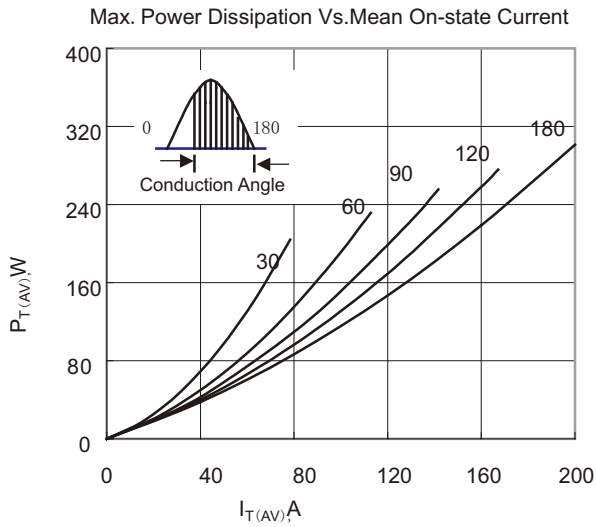
拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sinewave 50Hz single side cooled, T _c =90°C	125			350	A
I _{T(RMS)}	RMS on-state current		125			550	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V _{DRM} &V _{RRM} tp=10ms V _{DSM} &V _{RSM} = V _{DRM} &V _{RRM} +200V	125	800		1800	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			10	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			11.5	KA
I ² T	I ² T for fusing coordination	V _R =60%V _{RRM}				910	A ² s*10 ³
V _{TO}	Threshold voltage		125			0.80	V
r _T	On-state slop resistance					1.15	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =1050A	125			1.60	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =67%V _{DRM}	125			800	V/μs
di/dt	Critical rate of rise of off-state current	GATE SOURCE 1.5A , tr≤1 μs	125			100	A/μs
I _{GT}	Gate trigger current			30		150	mA
V _{GT}	Gate trigger voltage	V _A =12V, I _A =1A		0.7		2.0	V
I _H	Holding current			20		100	mA
V _{GD}	Non-trigger gate voltage	At 67%V _{DRM}	125			0.2	V
R _{th(j-c)}	Thermal resistance junction heatsink	single side cooled				0.065	°C /W
F _m	Thermal connection torque				40		N.m
T _{stg}	Stored temperature			-40		125	°C
Wt	Weight				600		g
Outline							

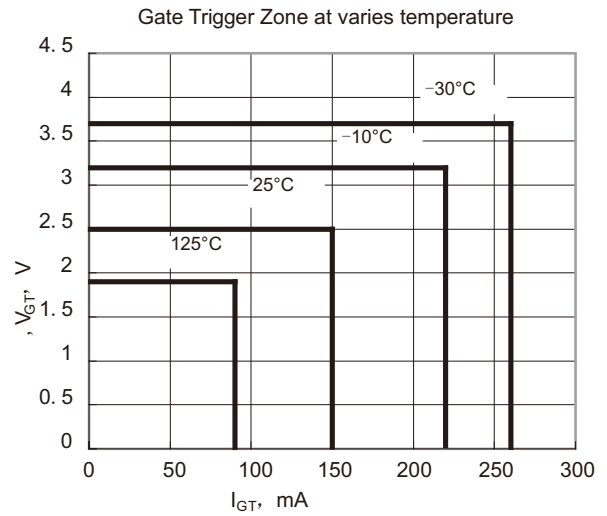
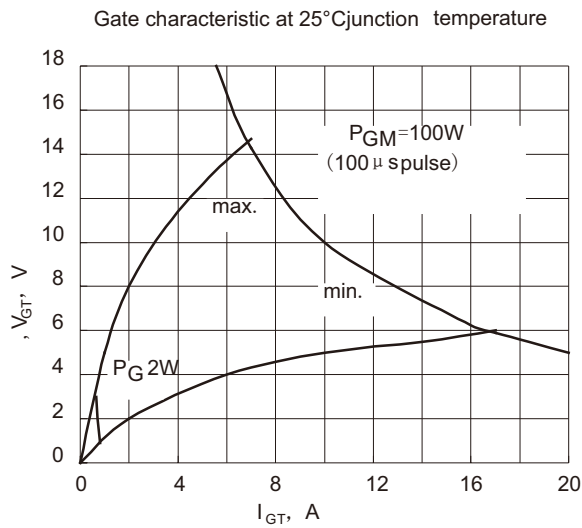
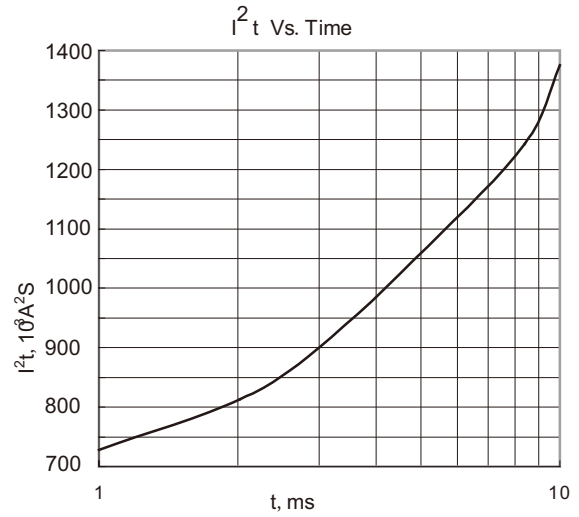
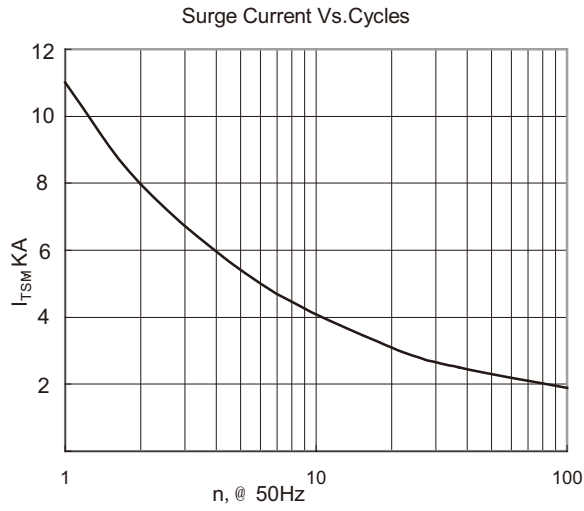
Rating and Characteristic



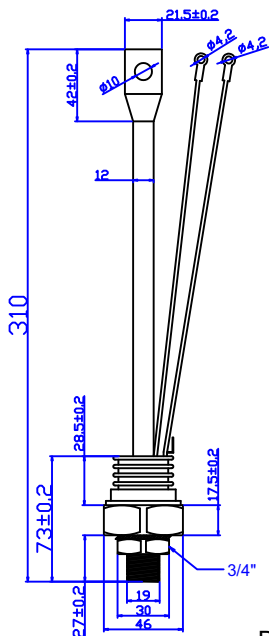
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Rating and Characteristic



OUTLINE



Dimensions (mm)

